



(12) **United States Design Patent** (10) **Patent No.:** **US D975,666 S**
Kondo et al. (45) **Date of Patent:** **** Jan. 17, 2023**

(54) **SEMICONDUCTOR MODULE**

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(**) Term: **15 Years**

(21) Appl. No.: **29/765,196**

(22) Filed: **Jan. 6, 2021**

(30) **Foreign Application Priority Data**

Jul. 31, 2020 (JP) 2020-015960 D

(51) **LOC (14) Cl.** **13-03**

(52) **U.S. Cl.**
 USPC **D13/182**

(58) **Field of Classification Search**
 USPC D13/101, 110, 112, 118, 120, 123, 133,
 D13/146, 147, 159, 154, 156, 174, 182,
 D13/184, 199; D14/356, 433, 435, 438
 CPC H01R 24/00; H01R 12/00; H01R 12/70;
 H01R 13/62

See application file for complete search history.

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(57) **CLAIM**

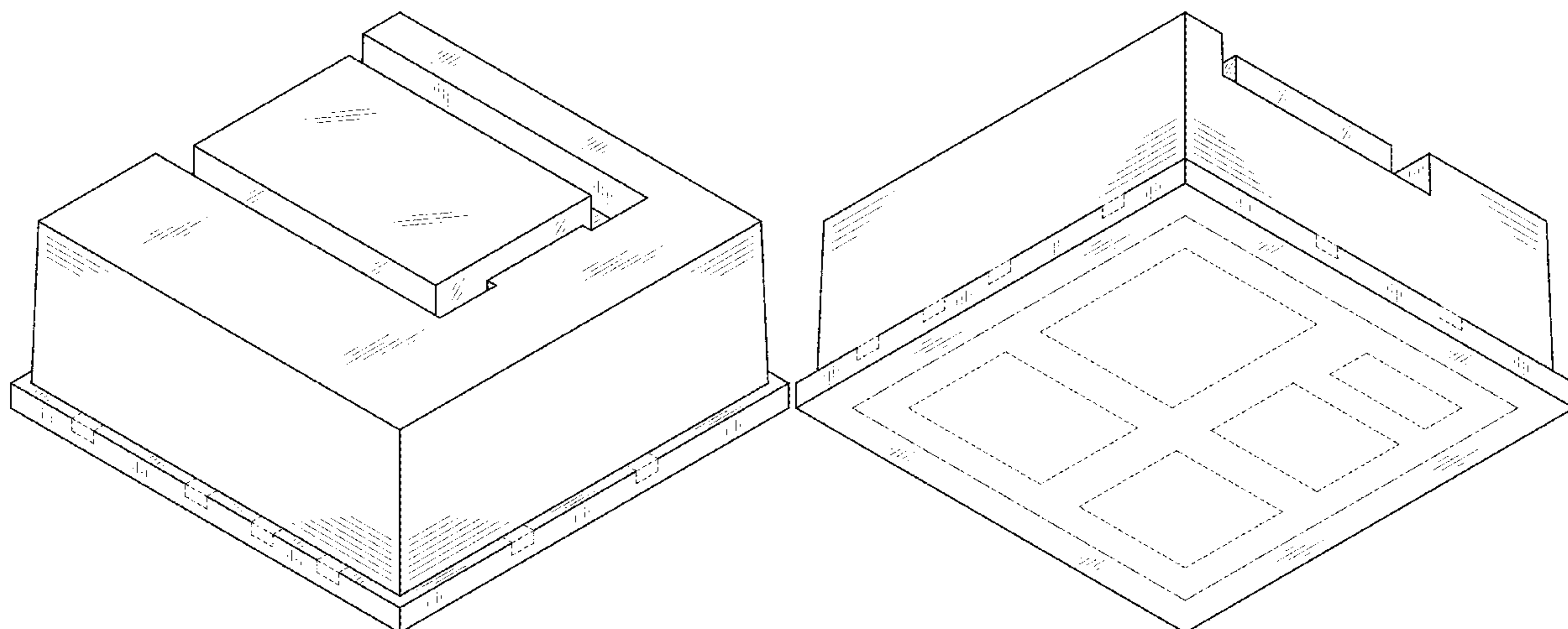
The ornamental design for a semiconductor module, as shown and described.

DESCRIPTION

FIG. 1 is a front, top and right side perspective view of a semiconductor module showing our new design; FIG. 2 is a rear, bottom and left side perspective view thereof; FIG. 3 is a front view thereof, the rear view being a mirror image of FIG. 3; FIG. 4 is a top plan view thereof; FIG. 5 is a bottom plan view thereof; FIG. 6 is a right side view thereof; and, FIG. 7 is a left side view thereof.

The broken lines illustrate portions of the semiconductor module that form no part of the claimed design. The dash-dotted lines denote the boundary of the claim and form no part of the claimed design. The member illustrated with fine, diagonal, parallel lines is translucent.

1 Claim, 7 Drawing Sheets



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FIG.1

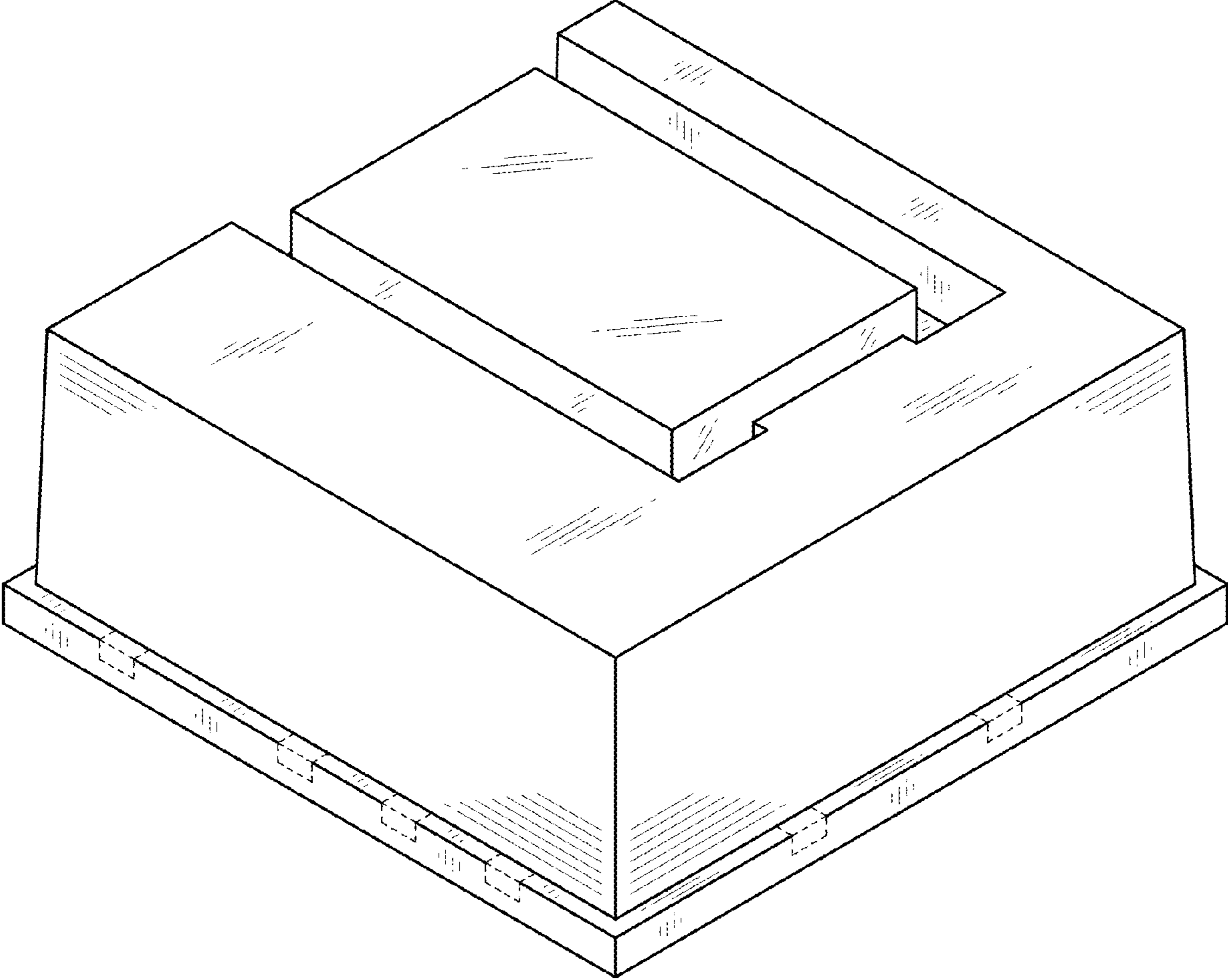


FIG.2

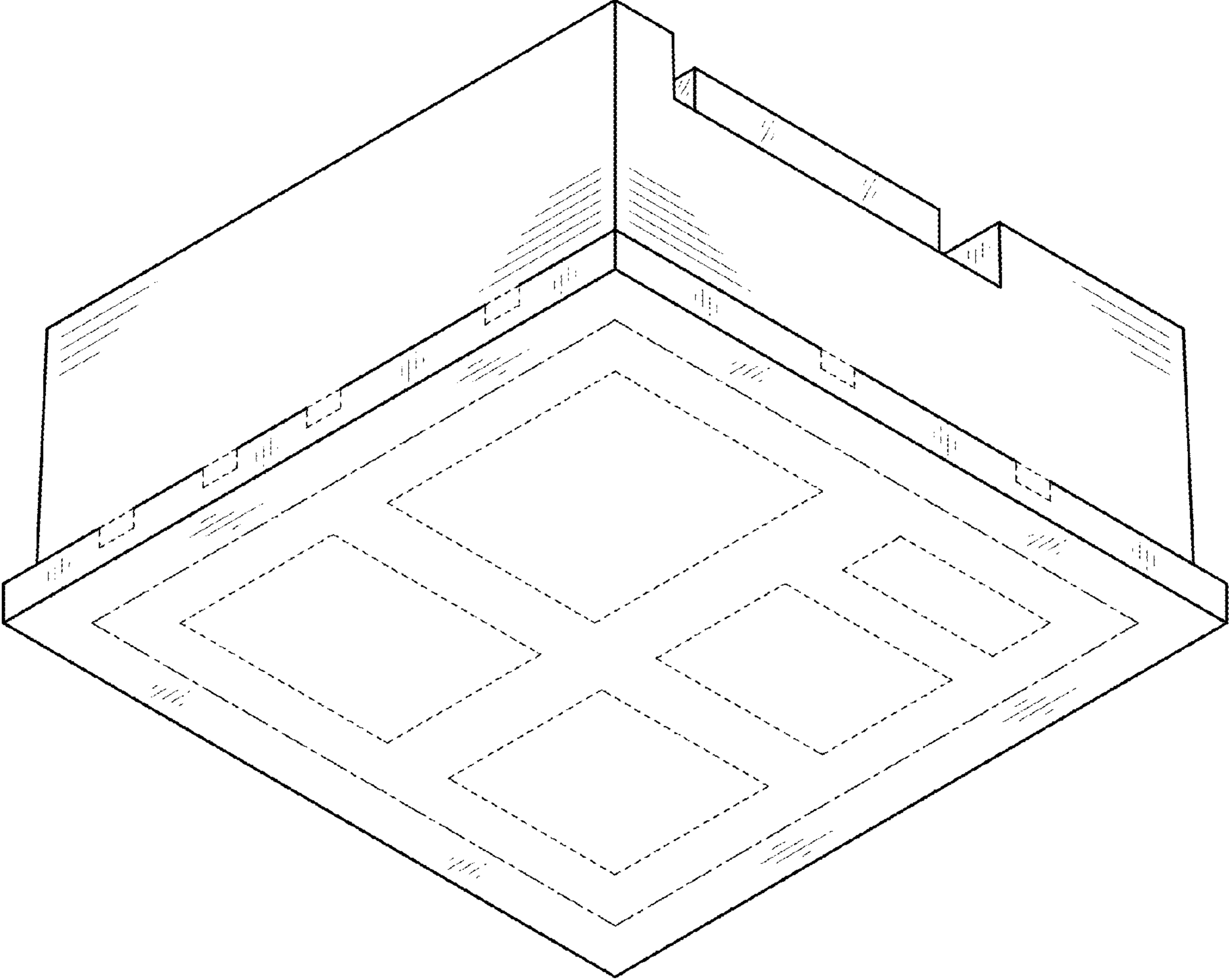


FIG.3

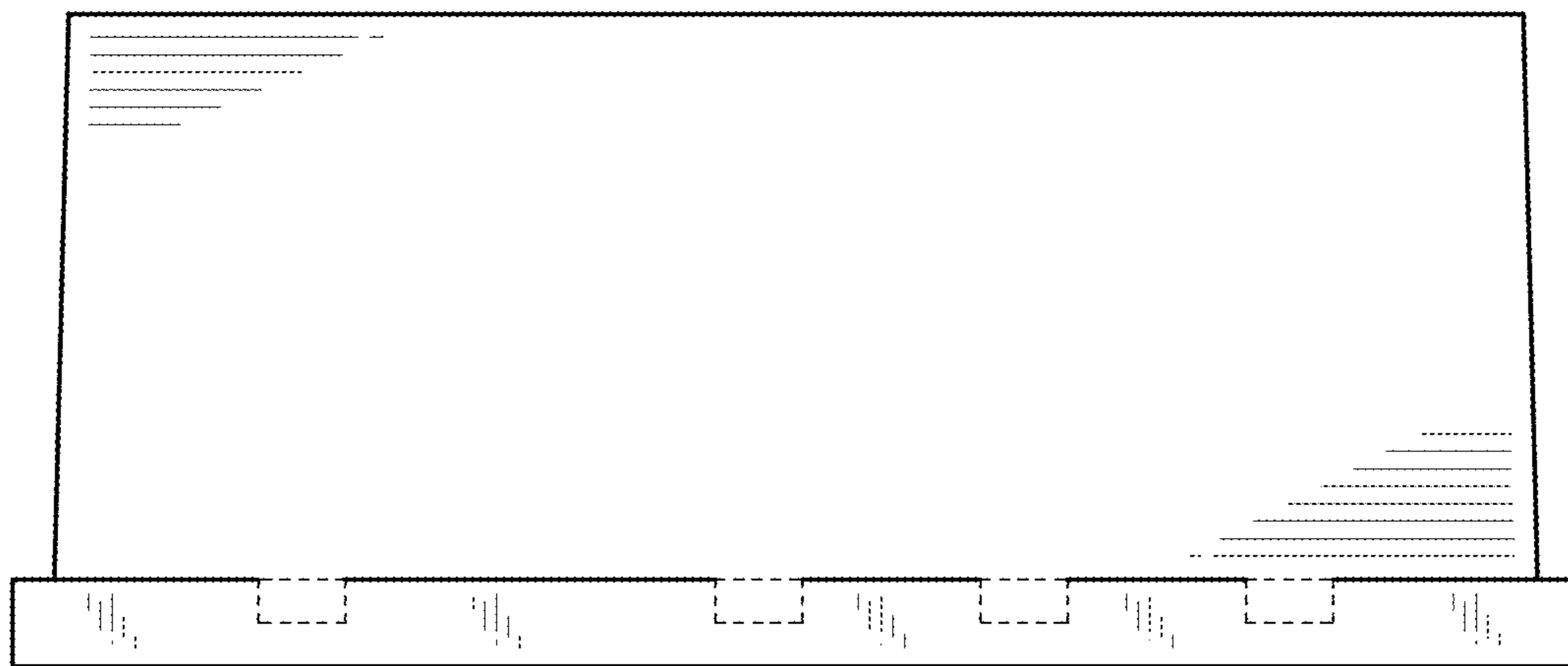


FIG.4

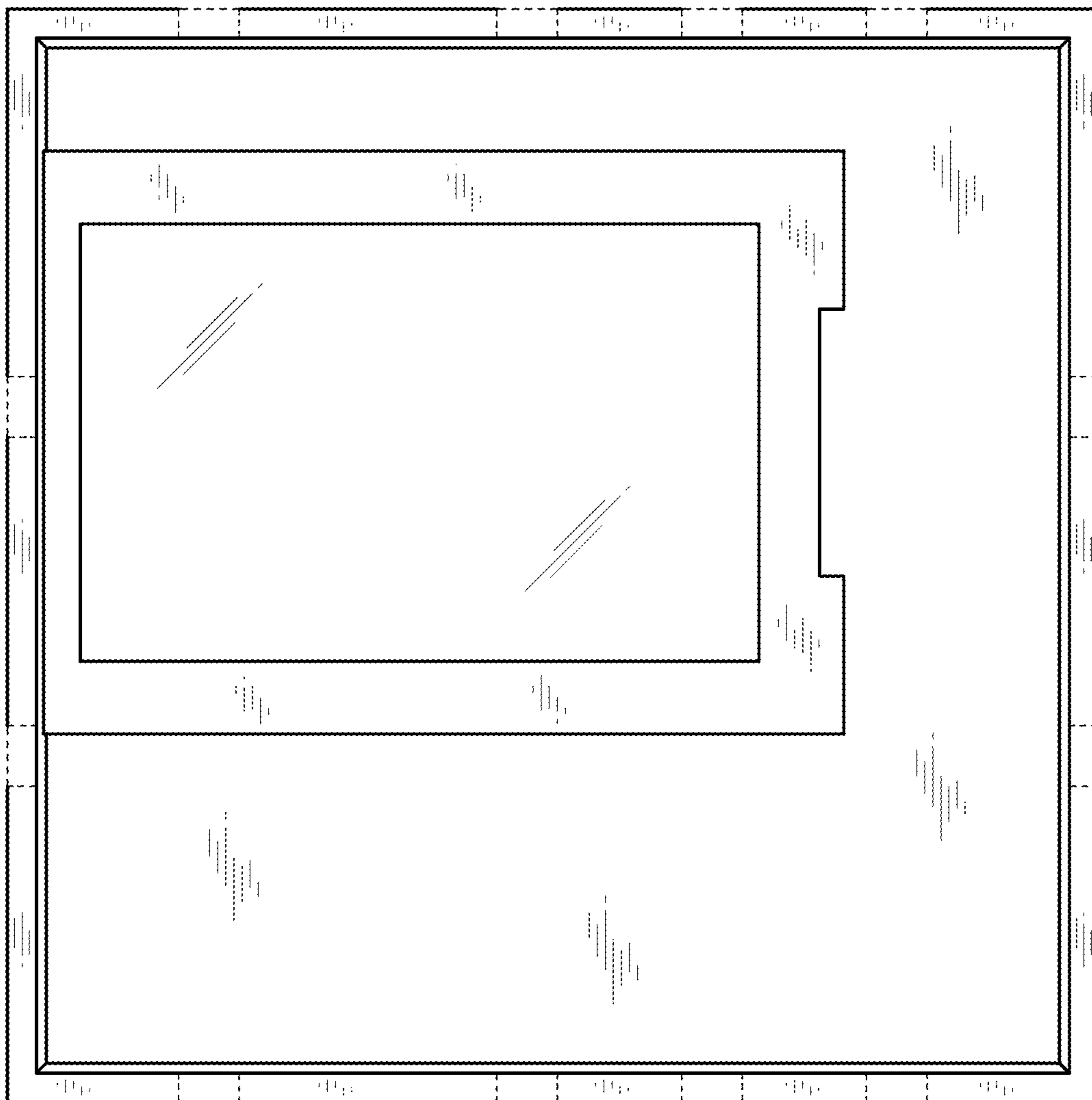


FIG.5

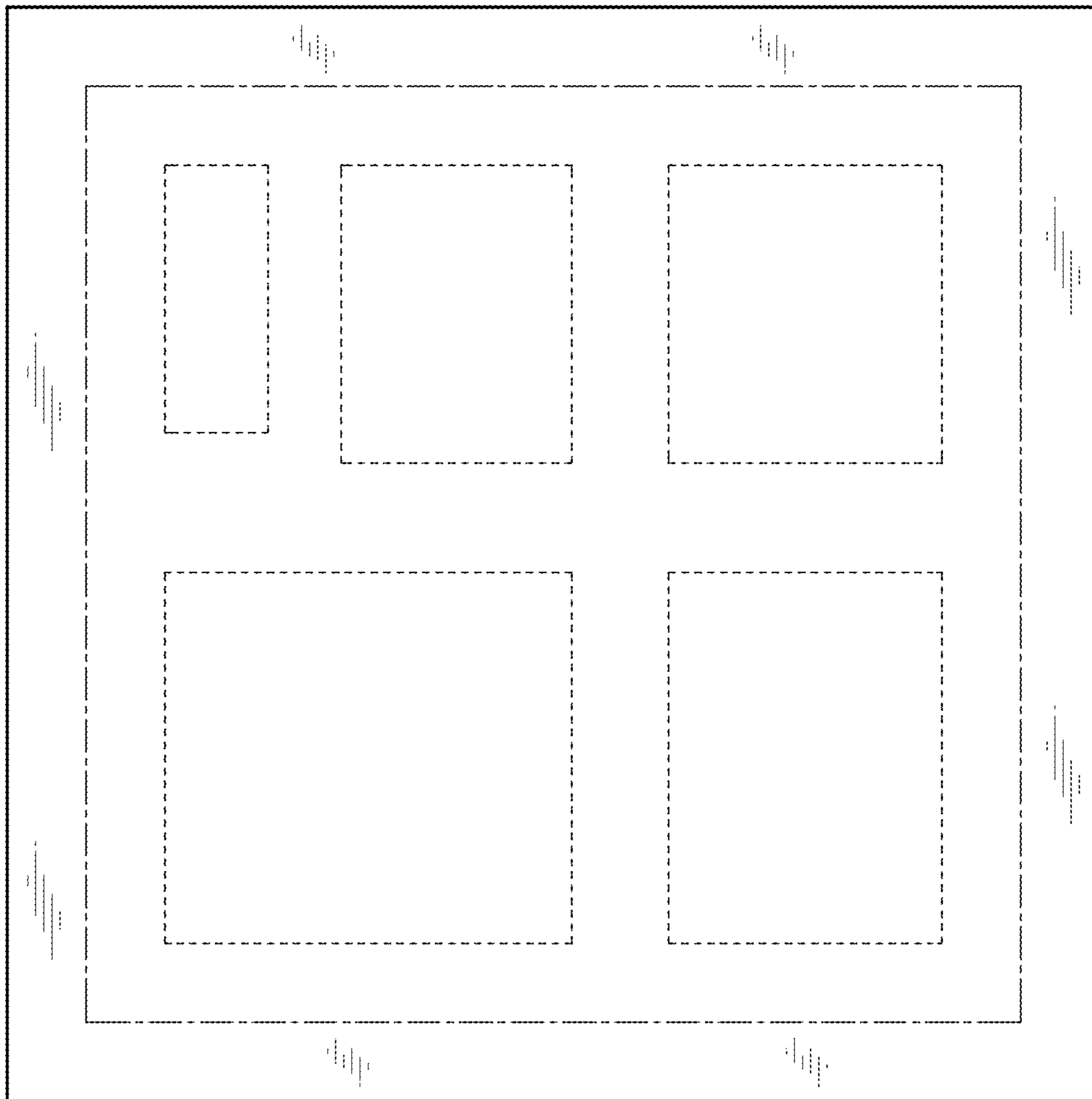


FIG.6

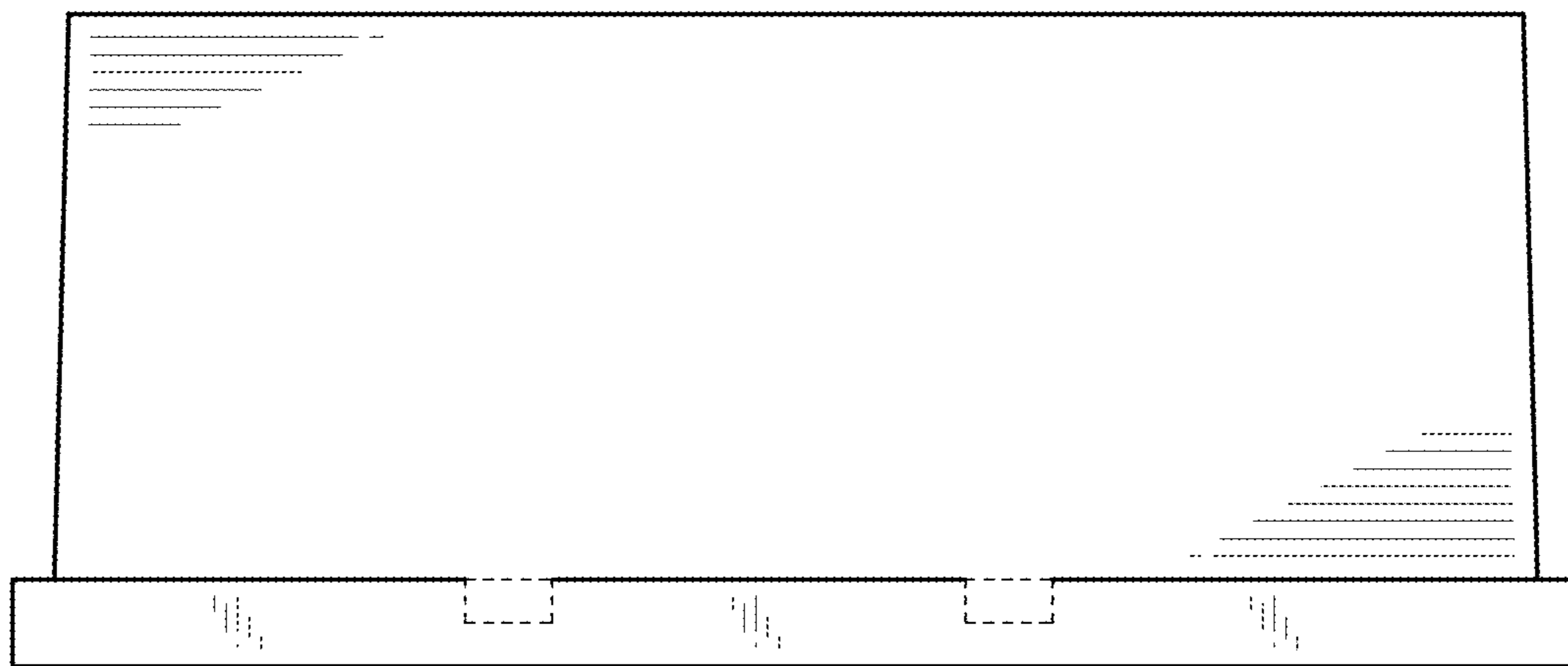


FIG.7

